

**Product specification** 

## **Plastic Silicon Controlled Rectifiers**

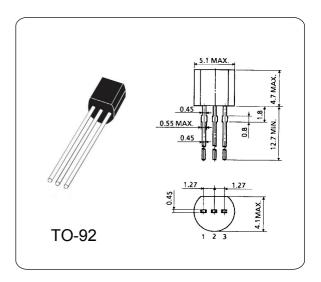
03P4M

## **GENERAL DESCRIPTION**

PNPN devices designed for high volume, linepowered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-92 package which isreladily adaptable for use in automatic insertion equipment.

## ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C)

Parameter	Symbol	Тур	Unit	
Repetitive peak off-state voltages	$egin{array}{c} egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}$	400	V	
Average on-state current	I <sub>T(AV)</sub>	0.3	Α	
RMS on-state current	I <sub>T(RMS)</sub>	0.47	Α	
Non-repetitive peak on-state current	I <sub>TSM</sub>	8.0	Α	
Max. Operating Junction Temperature	T <sub>j</sub>	110	°C	
Storage Temperature	T <sub>stg</sub>	-45~150	°C	



## **ELECTRICAL CHARACTERISTICS (Ta = 25 °C)**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Repetitive peak off-state voltages	$egin{array}{c} egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}$		400	_	_	V
Average on-state current	I <sub>T(AV)</sub>	half sine wave; T <sub>mb</sub> < 103 °C	_	0.3		Α
RMS on-state current	I <sub>T(RMS)</sub>	all conduction angles	_	0.47		Α
On-state voltage	V <sub>T</sub>	I <sub>T</sub> =4.0 A	_	_	2.5	V
Holding current	I <sub>H</sub>	V <sub>DM</sub> =24 V; I <sub>TM</sub> = 4.0A	_	_	5	mA
Latching current	IL	$V_D = 6.0 \text{ V}; I_{GT} = 20 \text{ mA}$	_	0.6	6	mA
Gate trigger current	I <sub>GT</sub>	$V_D = 6.0 \text{ V}; R_L = 100 \Omega$	_	15	200	uA
Gate trigger voltage	V <sub>GT</sub>	$V_{D}$ =6.0 V; $R_{L}$ = 100 $\Omega$	_	0.5	0.8	V